



August 2003

FDH15N50 / FDP15N50 / FDB15N50

15A, 500V, 0.38 Ohm, N-Channel SMPS Power MOSFET

Applications

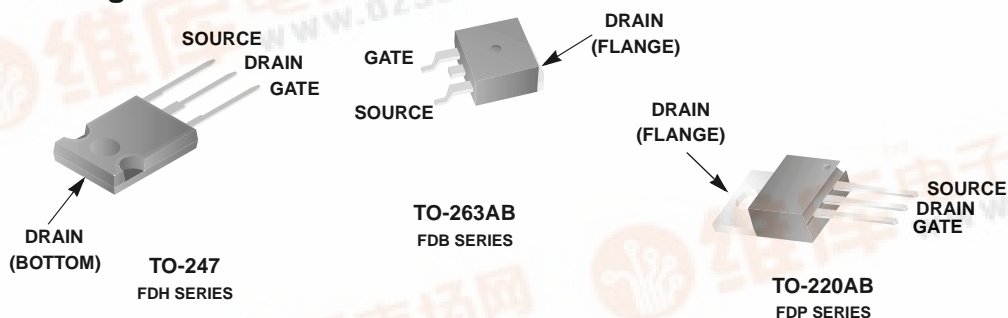
Switch Mode Power Supplies(SMPS), such as

- PFC Boost
- Two-Switch Forward Converter
- Single Switch Forward Converter
- Flyback Converter
- Buck Converter
- High Speed Switching

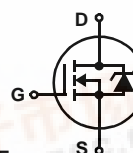
Features

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and High Reapplied dv/dt Ruggedness
- Reduced $r_{DS(ON)}$
- Reduced Miller Capacitance and Low Input Capacitance
- Improved Switching Speed with Low EMI
- 175°C Rated Junction Temperature

Package



Symbol



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	500	V
V_{GS}	Gate to Source Voltage	± 30	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$)	15	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 10\text{V}$)	11	A
	Pulsed ¹	60	A
P_D	Power dissipation	300	W
	Derate above 25°C	2	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$
	Soldering Temperature for 10 seconds	300 (1.6mm from case)	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	0.50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (TO-247)	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (TO-220, TO-263)	62	$^\circ\text{C/W}$



Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDH15N50	FDH15N50	TO-247	Tube	-	30
FDP15N50	FDP15N50	TO-220	Tube	-	50
FDB15N50	FDB15N50	TO-263	330mm	24mm	800

Electrical Characteristics $T_J = 25^\circ\text{C}$ (unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Statics

B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	500	-	-	V
$\Delta B_{VDSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	Reference to 25°C , $I_D = 1\text{mA}$	-	0.58	-	$\text{V}/^\circ\text{C}$
$r_{DS(ON)}$	Drain to Source On-Resistance	$V_{GS} = 10\text{V}$, $I_D = 7.5\text{A}$	-	0.33	0.38	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	3.4	4.0	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$, $T_C = 25^\circ\text{C}$	-	-	25	μA
		$V_{GS} = 0\text{V}$, $T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 30\text{V}$	-	-	± 100	nA

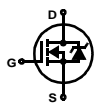
Dynamics

g_{fs}	Forward Transconductance	$V_{DD} = 10\text{V}$, $I_D = 7.5\text{A}$	10	-	-	S
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 10\text{V}$,	-	33	41	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 400\text{V}$,	-	7.2	10	nC
Q_{gd}	Gate to Drain "Miller" Charge	$I_D = 15\text{A}$	-	12	16	nC
$t_{d(ON)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}$,	-	9	-	ns
t_r	Rise Time	$I_D = 15\text{A}$,	-	5.4	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time	$R_G = 6.2\Omega$,	-	26	-	ns
t_f	Fall Time	$R_D = 17\Omega$	-	5	-	ns
C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	1850	-	pF
C_{OSS}	Output Capacitance		-	230	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	16	-	pF

Avalanche Characteristics

E_{AS}	Single Pulse Avalanche Energy ²		760	-	-	mJ
I_{AR}	Avalanche Current		-	-	15	A

Drain-Source Diode Characteristics

I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	15	A
I_{SM}	Pulsed Source Current ¹ (Body Diode)		-	-	60	A
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 15\text{A}$	-	0.86	1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 15\text{A}$, $di_{SD}/dt = 100\text{A}/\mu\text{s}$	-	470	730	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 15\text{A}$, $di_{SD}/dt = 100\text{A}/\mu\text{s}$	-	5	6.6	μC

Notes:

1: Repetitive rating; pulse width limited by maximum junction temperature

2: Starting $T_J = 25^\circ\text{C}$, $L = 7.0\text{mH}$, $I_{AS} = 15\text{A}$

Typical Characteristics

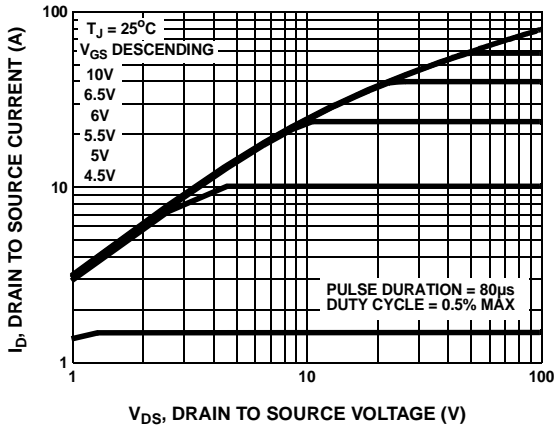


Figure 1. Output Characteristics

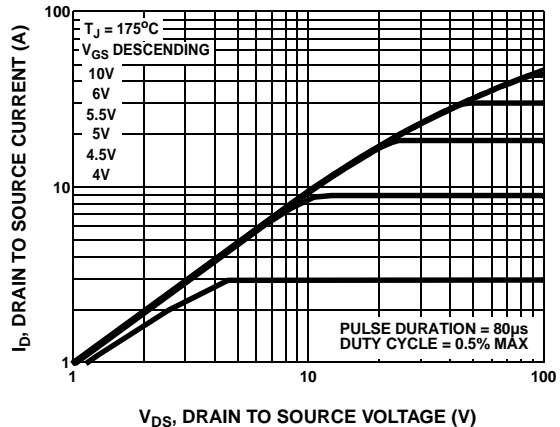


Figure 2. Output Characteristics

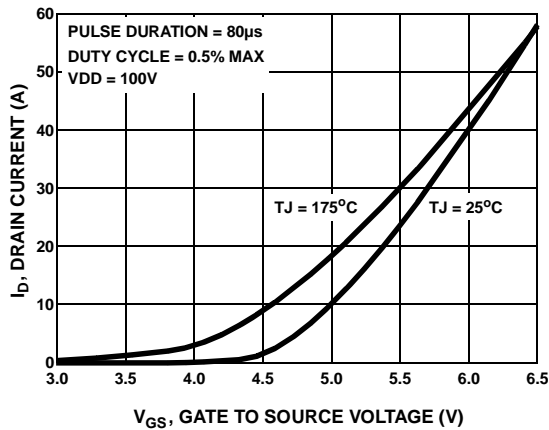


Figure 3. Transfer Characteristics

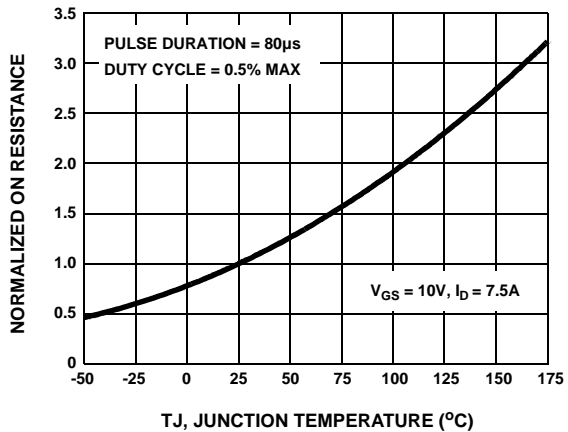


Figure 4. Normalized Drain To Source On Resistance vs Junction Temperature

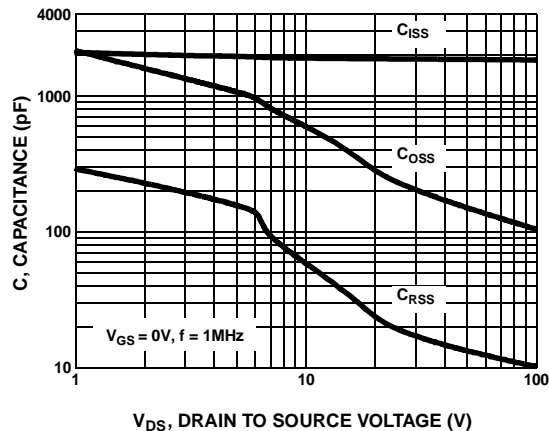


Figure 5. Capacitance vs Drain To Source Voltage

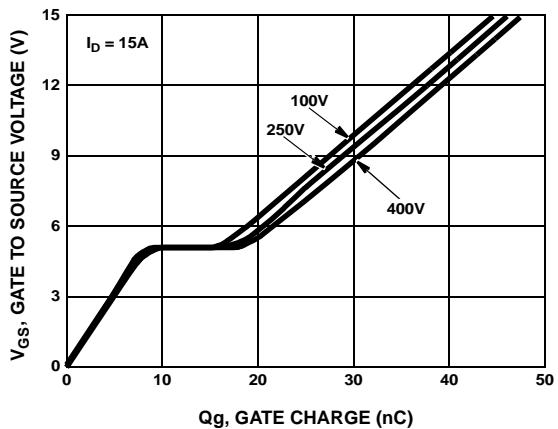


Figure 6. Gate Charge Waveforms For Constant Gate Current

Typical Characteristics

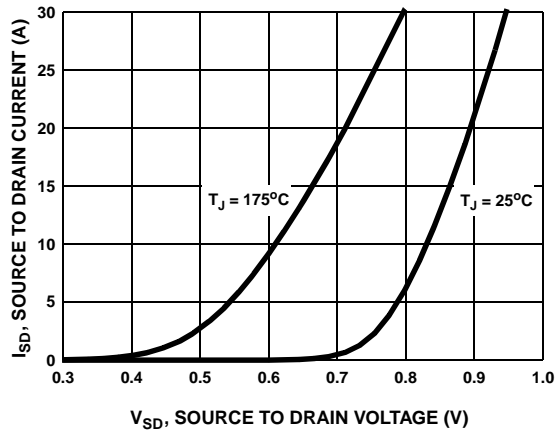


Figure 7. Body Diode Forward Voltage vs Body Diode Current

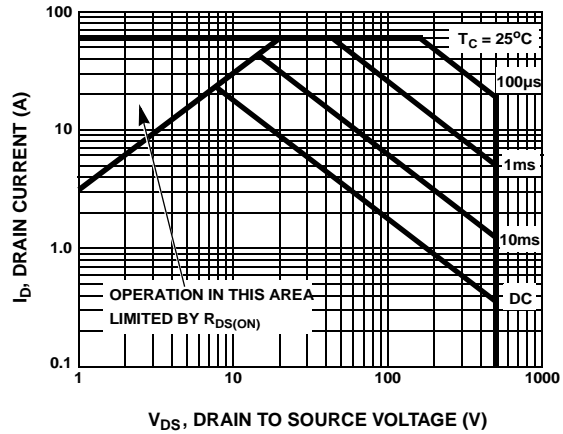


Figure 8. Maximum Safe Operating Area

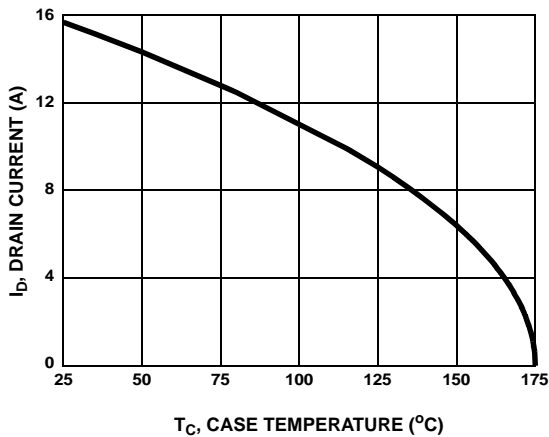


Figure 9. Maximum Drain Current vs Case Temperature

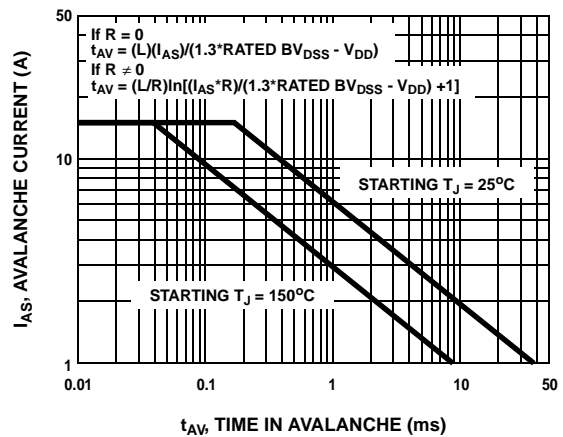


Figure 10. Unclamped Inductive Switching Capability

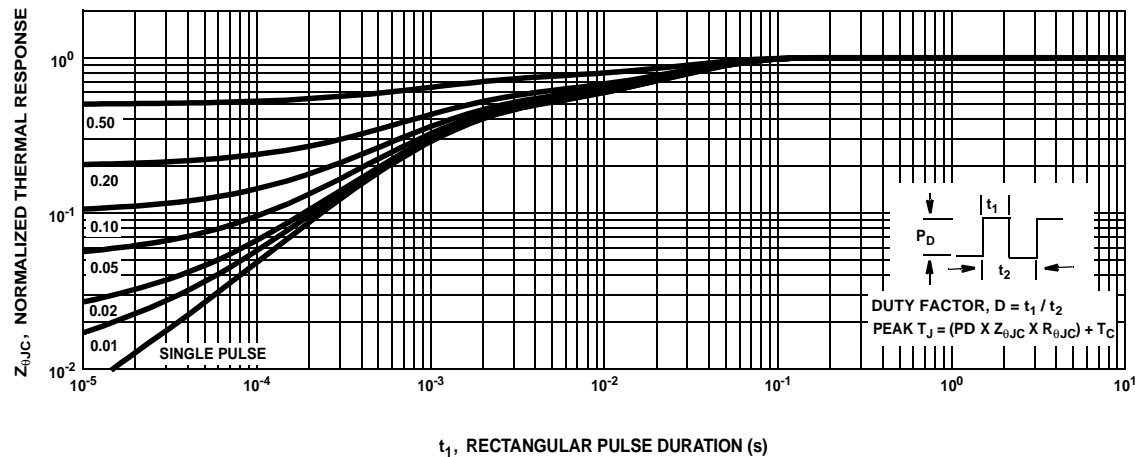


Figure 11. Normalized Transient Thermal Impedance, Junction to Case

Test Circuits and Waveforms

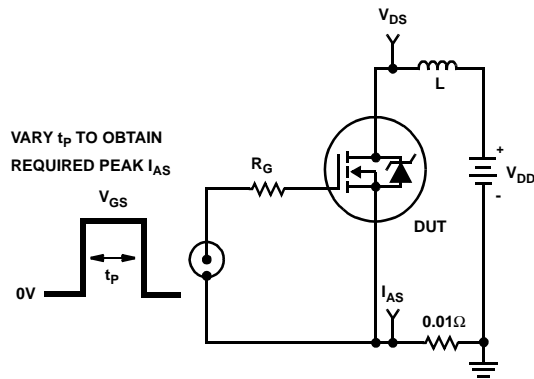


Figure 12. Unclamped Energy Test Circuit

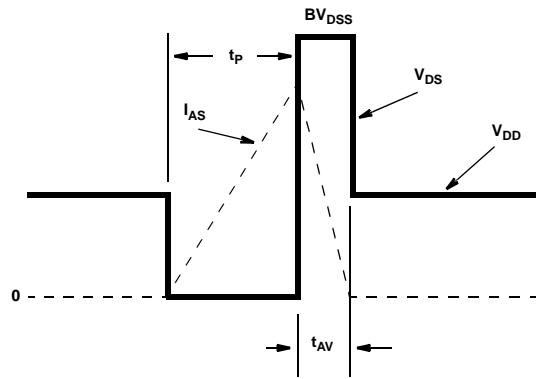


Figure 13. Unclamped Energy Waveforms

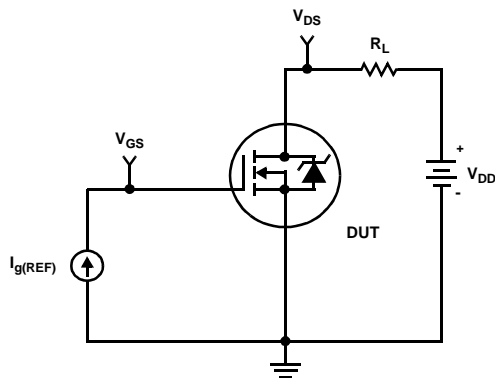


Figure 14. Gate Charge Test Circuit

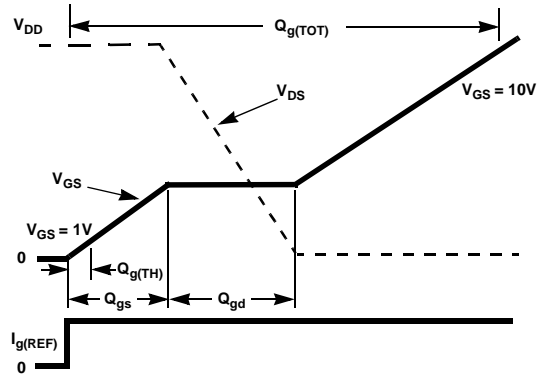


Figure 15. Gate Charge Waveforms

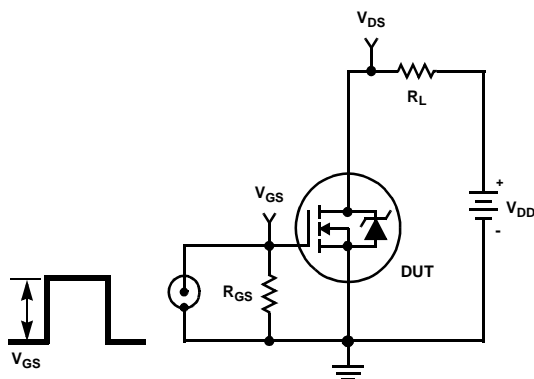


Figure 16. Switching Time Test Circuit

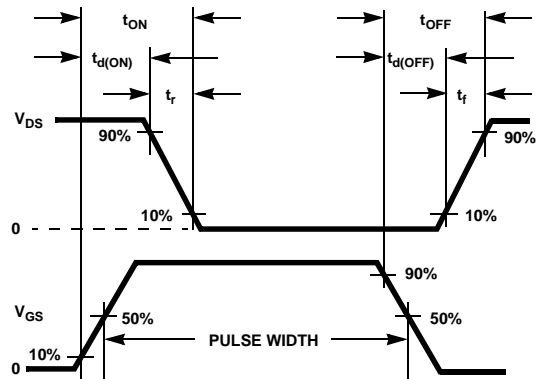


Figure 17. Switching Time Waveform

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CROSSVOLT™	FRFET™	MicroPak™	QFET®	SuperSOT™-8
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